VUPB006R350NA

Datasheet

35mΩ, 60V, N-Channel Power MOSFET VUPB006R350NA

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
60V	35mΩ@10V	20A

Symbol

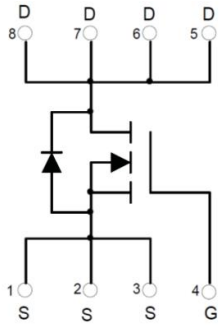
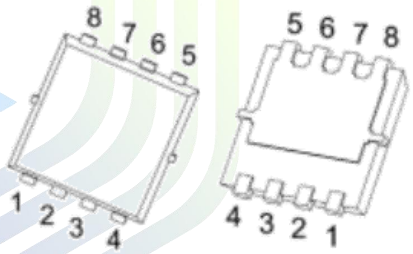


Figure 1 Symbol of VUPB006R350NA

Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- High ESD capability

Package Type



PDFN5X6-8L

Figure 2 Package Type of VUPB006R350NA

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

Ordering Information

Product Name	Package
VUPB006R350NA	PDFN5X6-8L

Absolute Maximum Ratings (T_C= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current Note1	I_D	20	A
Pulsed Drain Current Note2	I_{DM}	60	
Single Pulsed Avalanche Energy Note3	E_{AS}	70	mJ
Total Power Dissipation Note5	P_D	2.5	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient Note6	$R_{\theta JA}$		50		ºC/W

Electrical Characteristics (T_J= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 60V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note4]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	2	3	V
Static Drain-Source On-Resistance[Note4]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 10A		26	35	mΩ
Forward Transconductance[Note4]	g_{FS}	V_{DS}=6V, I_D= 10A	18			S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=30V		960		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		62		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		54		pF
Total Gate Charge	Q_g	V_{DS}=48V		12		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		4.1		nC
Gate-Drain Charge	Q_{gd}	I_D= 15A		4.5		nC
Gate Resistance	Rg	f = 1MHz, Open drain		1.1		Ω
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 30V		5		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		2.6		ns
Turn-off Delay Time	$t_{d(off)}$	R_L=15Ω		17		ns
Turn-off Fall Time	t_f	R_G=2.5Ω		2.5		ns
Diode Characteristics						
Diode Forward Voltage [Note4]	V_{SD}	V_{GS}=0V, I_S= 1A		0.72	1.2	V
Diode Continuous Forward Current	I_S	V_G=V_D=0V Force Current			20	A

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs

3.E_{AS} condition: V_{DD} = 30V,V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.

4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

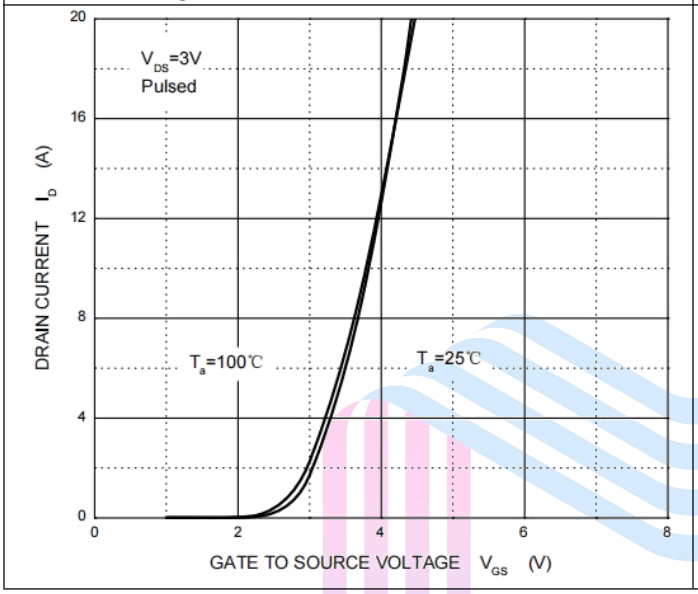


Figure 4: Output Characteristics

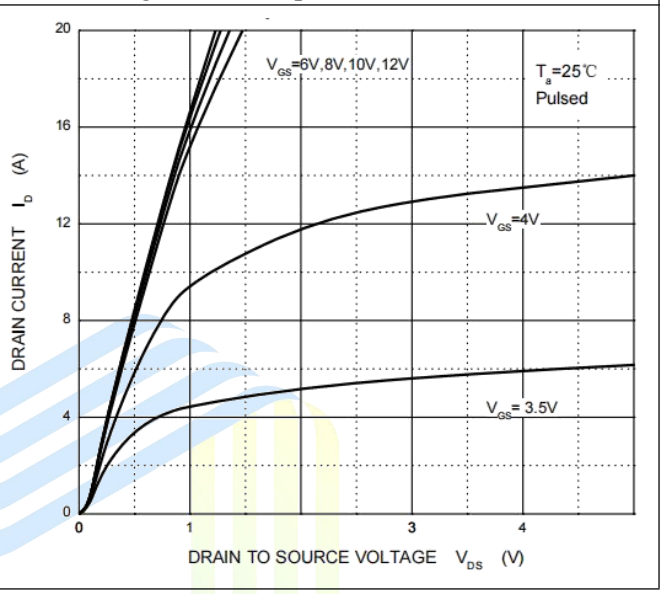


Figure 5: On-Resistance vs. Drain Current

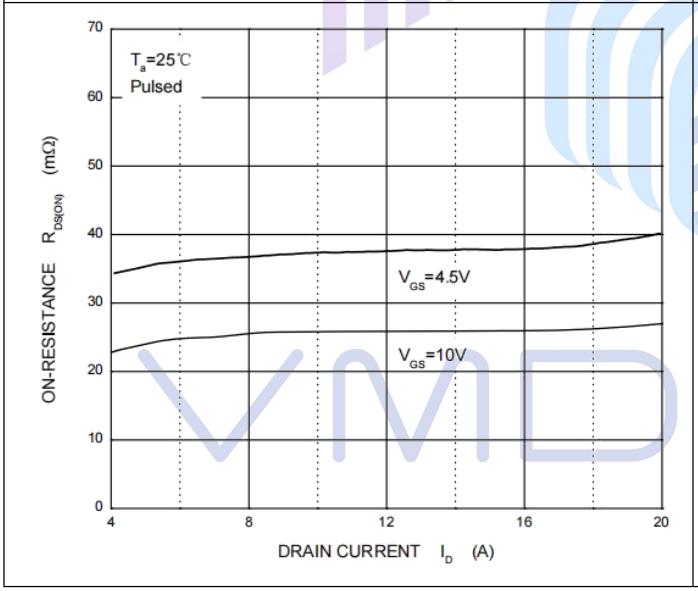


Figure 6: On-Resistance vs. Gate Voltage

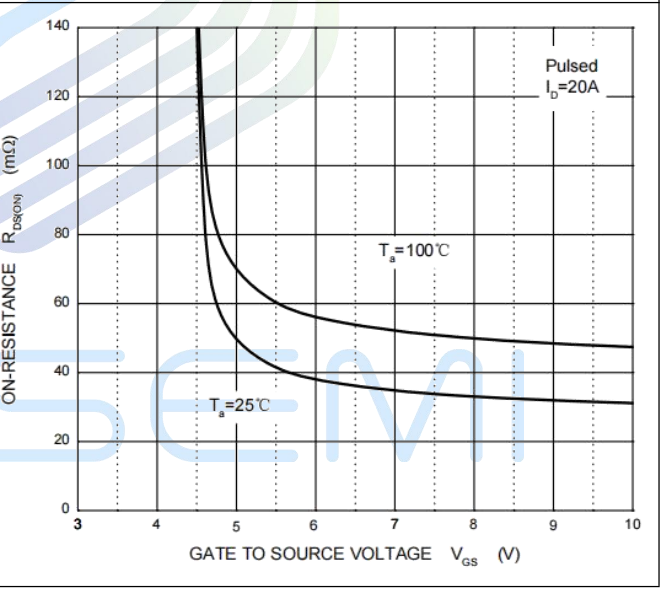


Figure 7: Body Diode Characteristics

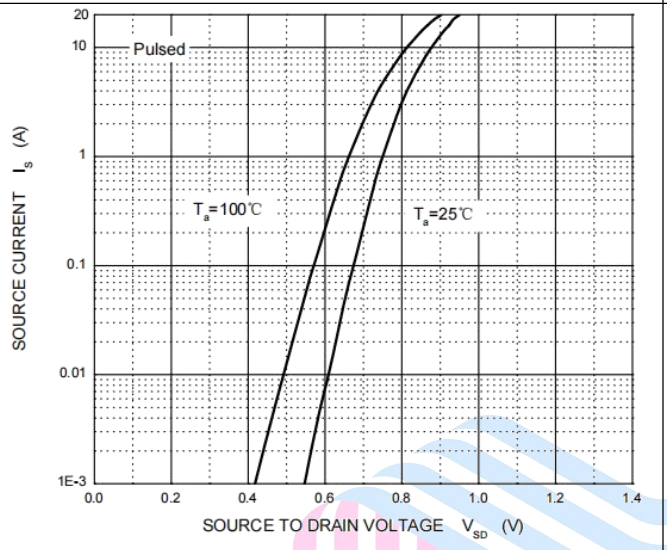
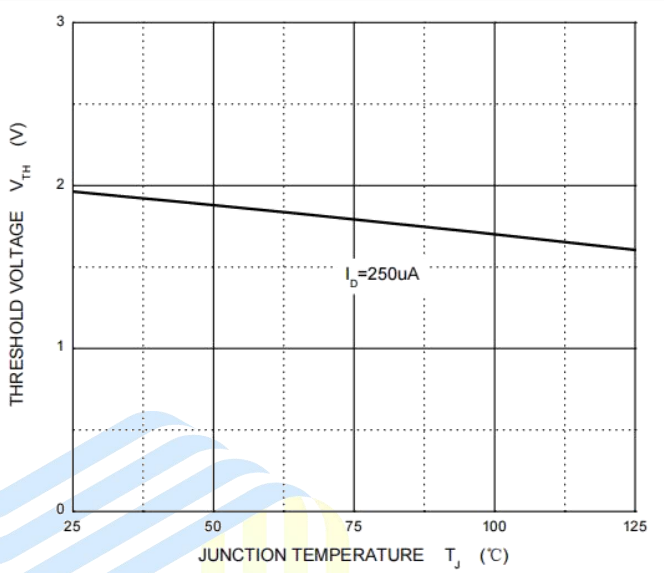
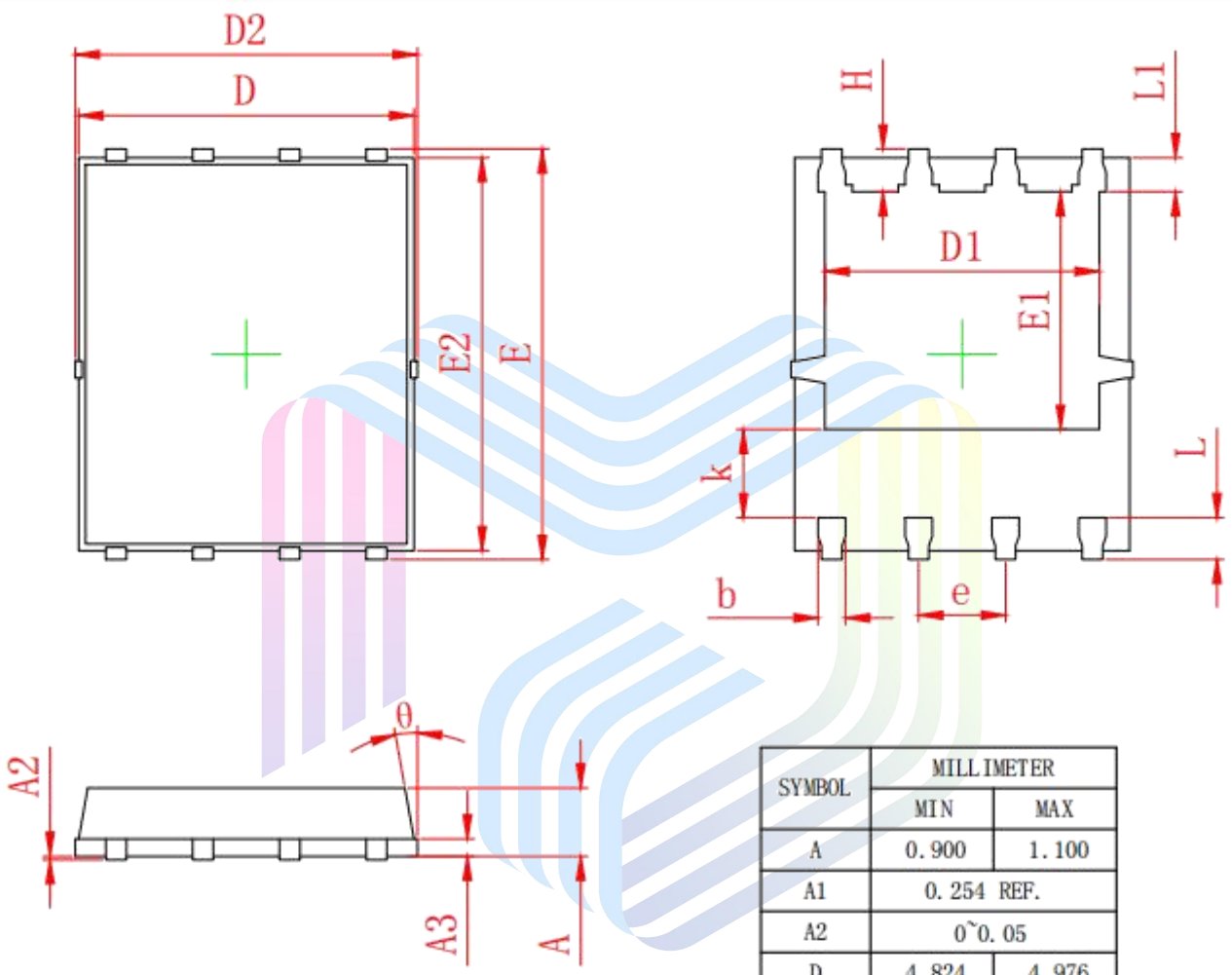


Figure 8: Threshold Voltage



Mechanical Dimensions:

PDFN5X6-8L Package Information



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.254 REF.	
A2	0~0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270 TYP.	
L	0.534	0.686
L1	0.424	0.576
k	1.190	1.390
H	0.549	0.701
θ	8°	12°

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